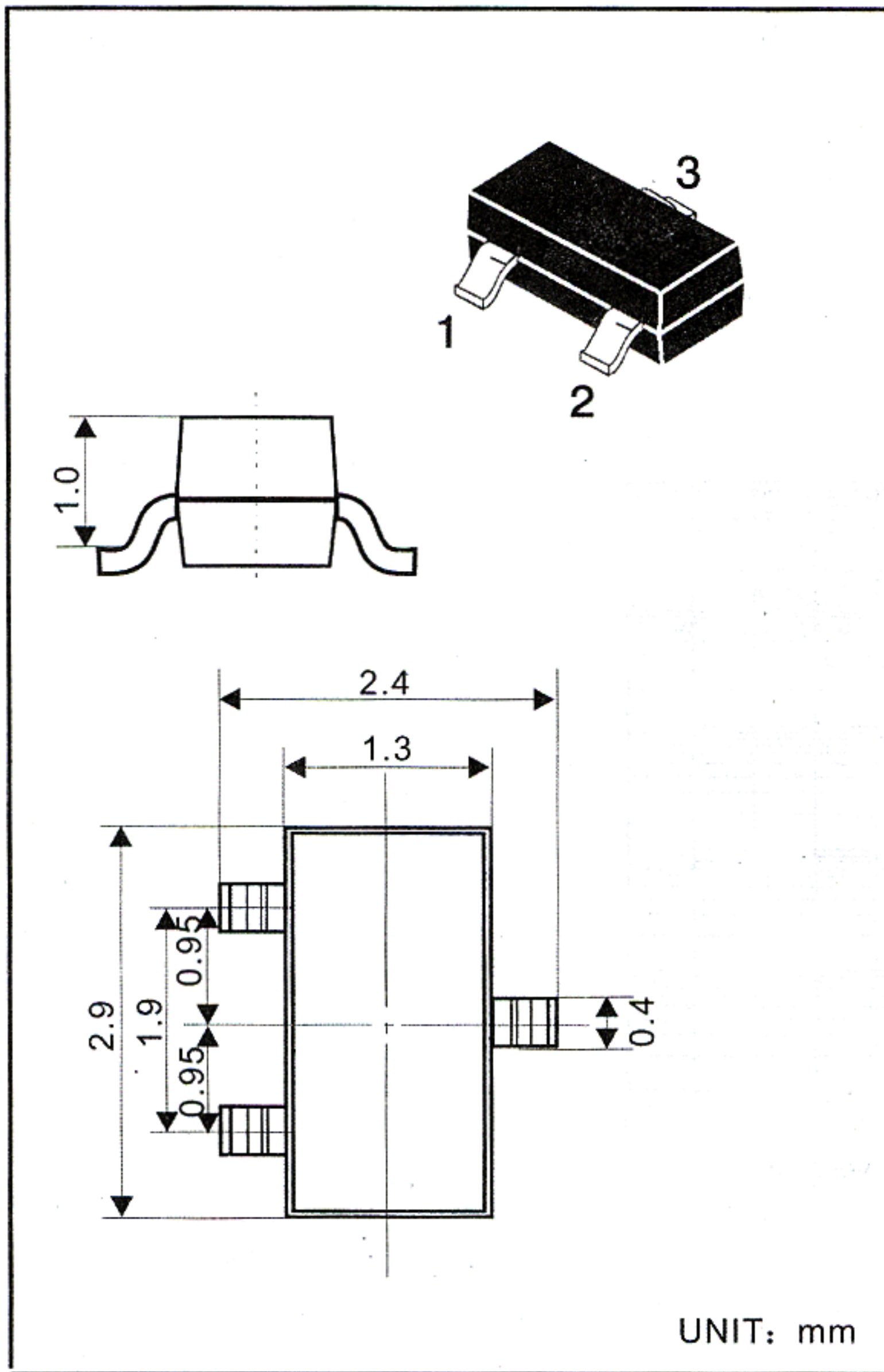


## 1SS196 SWITCHING DIODE



### FEATURES

**Power dissipation**

$P_d$ : 150mW ( $T_{amb}=25^{\circ}C$ )

**Forward current**

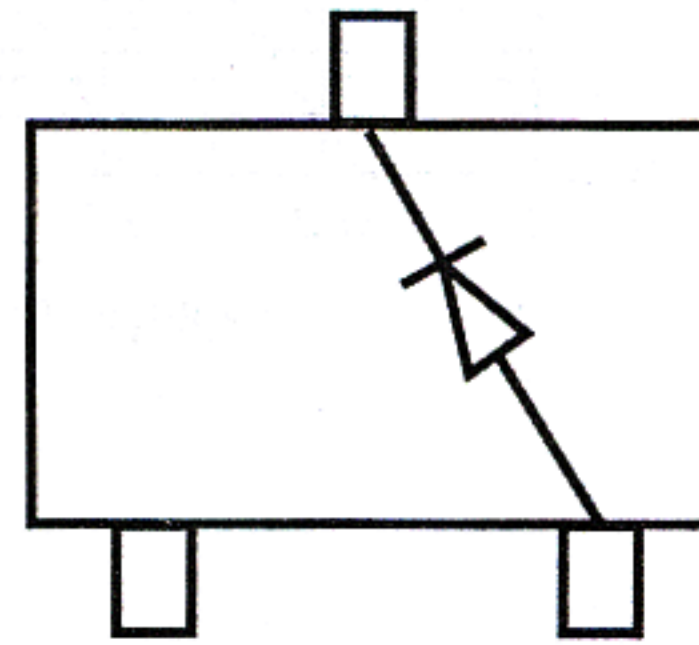
$I_F$ : 100mA

**Reverse voltage**

$V_R$ : 80V

**Operating and storage junction temperature range**

$T_{J,Tstg}$ :  $-55^{\circ}C$  to  $+150^{\circ}C$



MARKING: G3

### ELECTRICAL CHARACTERISTICS

( $T_{amp}=25^{\circ}C$  unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)}$	$I_R=100\mu A$	80		V
Reverse voltage leakage current	$I_R$	$V_R=80V$		0.5	$\mu A$
Forward voltage	$V_F$	$I_F=100mA$		1.2	V
Diode capacitance	$C_{tot}$	$V_R=0V, f=1MHz$		4	pF
Reverse recovery time	$t_{rr}$	$I_F=I_R=10mA$ $I_{rr}=0.1I_R$		4	ns



